40V PNP MEDIUM POWER HIGH GAIN TRANSISTOR IN D-PAK

SUMMARY

 BV_{CEO} = -40V : R_{SAT} = 83m Ω ; I_{C} = -3A

DESCRIPTION

Packaged in the D-Pak outline this high gain 40V PNP transistor offers low on state losses making it ideal for use in DC-DC circuits and various driving and power management functions.



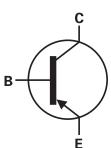
DPAK

FEATURES

- 3 Amps continuous current
- Up to 6 Amps peak current
- Low saturation voltages
- High gain

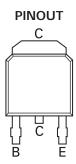
APPLICATIONS

- DC DC Converters
- MOSFET gate drivers
- · Charging circuits
- Power switches
- Siren drivers



ORDERING INFORMATION

DEVICE	REEL SIZE	TAPE WIDTH	QUANTITY PER REEL	
ZXT790AKTC	13"	16mm embossed	2500 units	



DEVICE MARKING

ZXT790A



ABSOLUTE MAXIMUM RATINGS

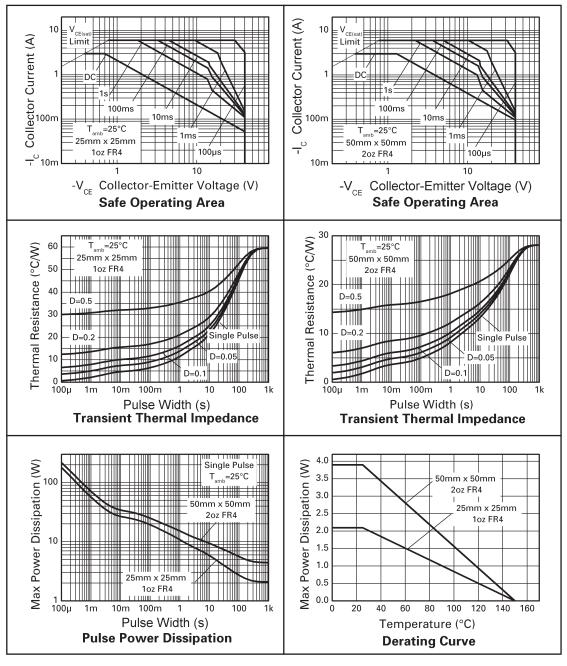
PARAMETER	SYMBOL	LIMIT	UNIT
Collector-Base Voltage	BV _{CBO}	-50	V
Collector-Emitter Voltage	BV _{CEO}	-40	V
Emitter-Base Voltage	BV _{EBO}	-5	V
Continuous Collector Current	I _C	-3	А
Peak Pulse Current	I _{CM}	-6	А
Base Current	I _B	-0.5	А
Power Dissipation at TA =25°C (a)	P _D	2.1	W
Linear Derating Factor		16.8	mW/°C
Thermal Resistance Junction to Ambient		59	°C/W
Power Dissipation at TA =25°C (b)	P _D	3.0	W
Linear Derating Factor		24.4	mW/°C
Thermal Resistance Junction to Ambient		41	°C/W
Power Dissipation at TA =25°C (c)	P _D	3.9	W
Linear Derating Factor		30.9	mW/°C
Thermal Resistance Junction to Ambient		32	°C/W
Operating and Storage Temperature Range	T _j , T _{stg}	-55 to 150	°C

NOTES

- (a) For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.
- (b) For a device surface mounted on 50mm x 50mm FR4 PCB with high coverage of single sided 1oz copper in still air conditions.
- (c) For a device surface mounted on 50mm x 50mm FR4 PCB with high coverage of single sided 2oz copper in still air conditions.



CHARACTERISTICS





ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}C$ unless otherwise stated)

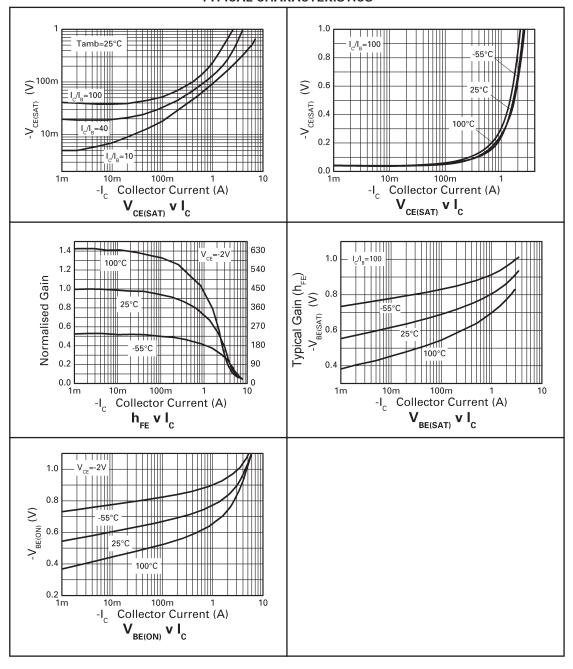
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS
Collector-Base Breakdown Voltage	BV _{CBO}	-50	-70		V	I _C = -100μA
Collector-Emitter Breakdown Voltage	BV _{CEO}	-40	-60		V	I _C = -10mA ⁽¹⁾
Emitter-Base Breakdown Voltage	BV _{EBO}	-5	-8.3		V	I _E = -100μA
Collector Cut-Off Current	I _{CBO}		<1	-20	nA	V _{CB} = -30V
Collector Cut-Off Current	I _{CE} S		<1	-20	nA	V _{CB} = -30V
Emitter Cut-Off Current	I _{EBO}		<1	-20	nA	V _{EB} = -4V
Collector-Emitter Saturation Voltage	V _{CE(SAT)}		-110	-170	mV	I _C = -0.5A, I _B = -5mA ⁽¹⁾
			-220	-350	mV	$I_C = -1A, I_B = -10mA^{(1)}$
			-260	-450		$I_C = -2A$, $I_B = -50mA^{(1)}$
			-250	-450	mV	$I_C = -3A$, $I_B = -300 \text{mA}^{(1)}$
Base-Emitter Saturation Voltage	V _{BE(SAT)}		-1.05	-1.15	V	I _C = -3A, IB = -300mA ⁽¹⁾
Base-Emitter Turn-On Voltage	V _{BE(ON)}		-0.9	-1.0	V	I _C = -3A, VCE = -2V ⁽¹⁾
Static Forward Current Transfer Ratio	h _{FE}	300	450	800		$I_C = -10 \text{mA}, V_{CE} = -2V^{(1)}$
		250	390			$I_C = -500 \text{mA}, V_{CE} = -2V^{(1)}$
		200	350			$I_C = -1A, V_{CE} = -2V^{(1)}$
		150	280			$I_C = -2A$, $V_{CE} = -2V^{(1)}$
		80	170			$I_C = -3A, V_{CE} = -2V^{(1)}$
Transition Frequency	f _T	100			MHz	I _C = -50mA, V _{CE} = -5V
						f = 50MHz
Output Capacitance	C _{OBO}		24		pF	V _{CB} = -10V, f = 1MHz ⁽¹⁾
Switching Times	t _{ON}		35		ns	$I_C = -500 \text{mA}, V_{CC} = -10 \text{V},$
	t _{OFF}		600		ns	$I_{B1} = I_{B2} = -50 \text{mA}$

NOTES

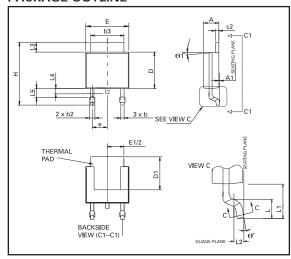
(1) Measured under pulsed conditions. Pulse width $\leq 300 \mu s$; duty cycle $\leq 2\%$.



TYPICAL CHARACTERISTICS



PACKAGE OUTLINE



Controlling dimensions are in millimetres. Approximate conversions are given in inches

DIM	MILLIMETRES		INCHES			
	MIN	MAX	MIN	MAX		
А	2.18	2.38	0.086	0.094		
A1	_	0.127	_	0.005		
b	0.635	0.89	0.025	0.035		
b2	0.762	1.114	0.030	0.045		
b3	5.20	5.46	0.205	0.215		
С	0.457	0.609	0.018	0.024		
c2	0.457	0.584	0.018	0.023		
D	5.97	6.22	0.235	0.245		
D1	5.20	_	0.205	_		
E	6.35	6.73	0.250	0.265		
E1	4.32	_	0.170	_		
е	2.30 BSC		0.090 BSC			
Н	9.40	10.41	0.370	0.410		
L	1.40	1.78	0.055	0.070		
L1	2.74 REF		0.108 REF			
L2	0.051 BSC		0.020 BSC			
L3	0.89	1.27	0.035	0.050		
L4	0.635	1.01	0.025	0.040		
L5	1.14	1.52	0.045	0.060		
θ1°	0°	10°	0°	10°		
θ°	0°	15°	0°	15°		

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